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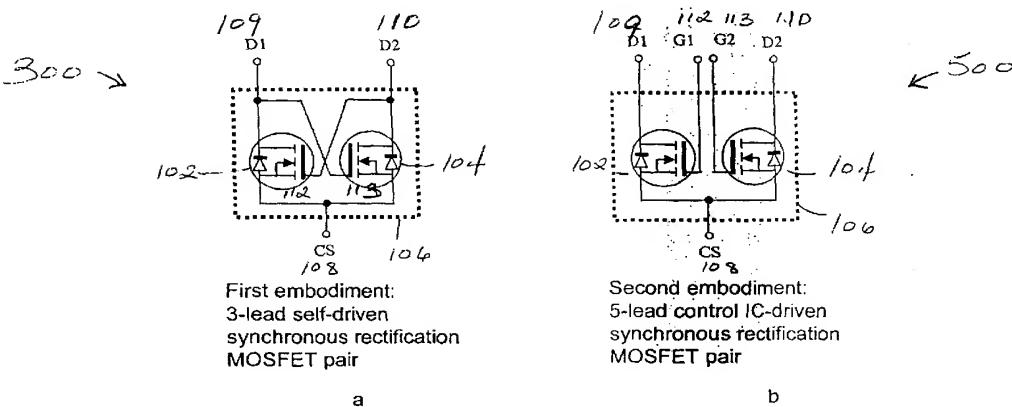
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(54) Title: MONOLITHIC POWER SEMICONDUCTOR STRUCTURES



First embodiment:  
3-lead self-driven  
synchronous rectification  
MOSFET pair

Second embodiment:  
5-lead control IC-driven  
synchronous rectification  
MOSFET pair

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(57) Abstract: Provided herein are exemplary embodiments of monolithic semiconductor structures having at least two lateral constructed semiconductor devices combined on a single semiconductor substrate.